

ABSTRACT

CHALCOGENIDE MATERIAL AND ELECTRONIC DEVICE INCLUDING THE SAME

5

A chalcogenide material and an electronic device are provided. The chalcogenide material may include 1-10 atomic percent (at%) of silicon, 10-20 at% of germanium, 25-35 at% of arsenic, 40-50 at% of selenium, and 1-10 at% of tellurium. The electronic device may include a switching element including a chalcogenide material, the chalcogenide material including 1-10 atomic percent (at%) of silicon, 10-20 at% of germanium, 25-35 at% of arsenic, 40-50 at% of selenium, and 1-10 at% of tellurium; a first electrode electrically coupled to the switching element; and a second electrode electrically coupled to the switching element.

FIG. 7D